

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	0	2001/016605	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:10	
2	BRS	L2	0	2001/0160605	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:11	
3	BRS	L3	24	"0160605"	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:11	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	1	2002/0160605	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:16	
5	BRS	L5	13981	kanazawa	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:16	
6	BRS	L6	0	5 and (huv-cvd or huv near cvd)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:17	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	0	5 and (huv-cvd) or (huv near cvd)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:18	
8	BRS	L8	0	5 and (uvh-cvd) or (uvv near cvd)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:18	
9	BRS	L9	430	5 and (uhv-cvd) or (uhv near cvd)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:18	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	90	5 and (uhv-cvd) or (uhv near cvd) near25 (gas)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:20	
11	BRS	L11	127	5 and (uhv-cvd) or (uhv near cvd) near25 (pressure)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:21	
12	BRS	L12	1	5 and (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (sic)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:21	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	1	5 and (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (temp\$5)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:22	
14	BRS	L14	4	5 and (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (carbon)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:23	
15	BRS	L15	297	(uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (carbon)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:08	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	297	(uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (carbon) near35 (temp\$5)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:23	
17	BRS	L17	297	(uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (carbon near5 gas) near35 (temp\$5)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:23	
18	BRS	L18	132	(wafer or substrate) near25 (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (carbon near5 gas) near35 (temp\$5)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 15:24	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
19	BRS	L19	15	(wafer or substrate) near25 (crystal\$3) near15 (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (carbon near5 gas) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:30	
20	BRS	L20	104	(wafer or substrate) near25 (crystal\$3 or silicon or si) near15 (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (carbon near5 gas) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:52	
21	BRS	L21	104	(wafer or substrate) near25 (silicon or si) near15 (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (carbon near5 gas) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:53	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
22	BRS	L22	104	(wafer or substrate) near25 (silicon or si) near15 (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (two near carbon near5 gas) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:54	
23	BRS	L23	104	(wafer or substrate) near25 (silicon or si) near15 (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (two near carbon near gas) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:55	
24	BRS	L24	104	(wafer or substrate) near25 (silicon or si) near15 (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (two near carbon) near (alloy or gas) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:55	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
25	BRS	L25	104	(wafer or substrate) near25 (silicon or si) near15 (uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (two near carbon) near (alloy) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:53	
26	BRS	L26	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 ((two near carbon) near (alloy)) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:56	
27	BRS	L27	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 (two near carbon) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:57	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
28	BRS	L28	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 (carbon or alloy) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:57	
29	BRS	L29	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 ((pressure) near25 (carbon or alloy)) near35 (temp\$5)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 15:58	
30	BRS	L30	2	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 (carbon or alloy)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:01	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
31	BRS	L31	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 (carbon near5 alloy)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:01	
32	BRS	L32	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 (silicon near3 alloy)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:01	
33	BRS	L33	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 (silicon near5 alloy)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:01	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
34	BRS	L34	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 ((silicon or si) near5 (alloy))	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:02	
35	BRS	L35	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 ((silicon or si) near25 (alloy))	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:03	
36	BRS	L36	0	(wafer or substrate) near25 (silicon or si) near15 ((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 ((silicon or si or carbon) near25 (alloy))	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:03	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
37	BRS	L37	15058	two near carbon near atom\$1	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 16:09	
38	BRS	L38	192	(two near carbon near atom\$1) near15 (gas)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 16:09	
39	BRS	L39	54	(two near carbon near atom\$1) near15 (gas near containing)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 16:45	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
40	BRS	L41	0	(double or triple) near10 (two near carbon near atom\$1) near15 (gas near containing) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:13	
41	BRS	L40	26	(two near carbon near atom\$1) near15 (gas near containing) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:15	
42	BRS	L42	26	(two near carbon near atom\$1) near15 (gas near containing) near15 (oxygen near15 atoms)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:18	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
43	BRS	L43	0	(two near carbon near atom\$1) near15 (gas near containing) near15 (oxygen) near15 (ethylene or acetylene)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 16:19	
44	BRS	L44	0	(two near carbon near atom\$1) near15 (gas near containing) near15 (oxygen) near15 (ethylene or acetylene)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 16:19	
45	BRS	L45	26	(two near carbon near atom\$1) near15 (gas near containing) near15 (oxygen)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 16:42	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
46	BRS	L46	73	(two or three) near (carbon near atom\$1) near15 (gas near containing)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:45	
47	BRS	L47	3459	(carbon near5 gas) near25 (ethyl\$3 or acetyl\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:56	
48	BRS	L49	4	(carbon near5 gas near5 crystal) near25 (ethyl\$3 or acetyl\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:00	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
49	BRS	L48	5	(carbon near5 gas near5 alloy) near25 (ethyl\$3 or acetyl\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:56	
50	BRS	L50	9	(carbon near5 gas near5 crystal) near25 (electrical\$2)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 16:57	
51	BRS	L51	419	(carbon near5 gas near5 oxygen) near25 (ethyl\$3 or acetyl\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:01	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
52	BRS	L52	0	(carbon near5 gas near5 oxygen) near25 (ethyl\$3 or acetyl\$3) near15 (less near than)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:01	
53	BRS	L53	2	(carbon near5 gas near5 oxygen) near25 (ethyl\$3 or acetyl\$3) near15 (less or than)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:04	
54	BRS	L54	0	(carbon near5 gas near5 oxygen) near25 (diborane or phosphine) near15 (less or than)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:04	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
55	BRS	L55	4	(gas near5 oxygen) near25 (diborane or phosphine) near15 (less or than)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:04	
56	BRS	L57	0	56 and (silicon near carbon)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:05	
57	BRS	L58	103	56 and (silicon or carbon)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:05	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
58	BRS	L56	136	(gas) near25 (diborane or phosphine) near15 (less or than)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:06	
59	BRS	L59	0	(gas) near25 (diborane near phosphine near arsine) near15 (less or than)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:07	
60	BRS	L60	3	(gas) near25 (diborane near5 phosphine near5 arsine) near15 (less or than)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:07	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
61	BRS	L61	11	(gas) near25 (diborane) near5 (phosphine or arsine) near15 (less or than)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:08	
62	BRS	L62	297	(uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (wafers)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:09	
63	BRS	L63	297	(uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (plurality ear3 wafers)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:09	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
64	BRS	L64	297	(uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (plurality near3 wafers)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:09	
65	BRS	L65	297	(uhv-cvd) or (uhv near cvd) near25 (pressure) near25 (plurality near wafers)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:09	
66	BRS	L66	1	((uhv-cvd) or (uhv near cvd)) near25 (pressure) near25 (plurality near wafers)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:10	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
67	BRS	L67	400	silicon near carbon near alloy	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:10	
68	BRS	L68	0	(silicon near carbon near alloy) near15 (poly and crystal\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:10	
69	BRS	L69	16	(silicon near carbon near alloy) near15 (poly or crystal\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:11	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
70	BRS	L70	76	(carbon near alloy) near15 (poly or crystal\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:11	
71	BRS	L71	1	(carbon near alloy) near15 (poly or crystal\$3) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:11	
72	BRS	L72	1933	(carbon or alloy) near15 (poly or crystal\$3) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:11	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
73	BRS	L73	1933	((carbon or alloy)) near15 (poly or crystal\$3) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:11	
74	BRS	L74	8	((carbon near5 alloy)) near15 (poly or crystal\$3) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:12	
75	BRS	L75	0	(carbon near alloy) near15 (poly) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:12	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
76	BRS	L76	20	(carbon near5 alloy) near15 (poly\$4) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:13	
77	BRS	L77	0	(carbon near5 alloy) near15 (polycrystal\$3) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:13	
78	BRS	L78	0	(carbon near5 alloy) near15 (poly-crystal\$3) near15 (oxygen)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/0 6 17:14	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
79	BRS	L79	8	(carbon near5 alloy) near15 (crystal\$3) near15 (oxygen)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/06 17:14	

	U	1	Document ID	Title	Current OR	Pages
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040161911 A1	Epitaxial and polycrystalline growth of Si _{1-x-y} GexCy and Si _{1-y} Cy alloy layers on Si by UHV-CVD	438/479	21
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040161875 A1	Epitaxial and polycrystalline growth of Si _{1-x-y} GexCy and Si _{1-y} Cy alloy layers on Si by UHV-CVD	438/105	21
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040092085 A1	Semiconductor crystal film and method for preparation thereof	438/479	19
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20030203599 A1	Semiconductor wafer and method for fabricating the same	438/478	12
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20030146473 A1	Semiconductor device	257/346	25
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20020189535 A1	Method for manufacturing semiconductor crystal film	117/105	13

	U	1	Document ID	Title	Current OR	Pages
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20020182423 A1	Epitaxial and polycrystalline growth of Si _{1-x-y} GexCy and Si _{1-y} Cy alloy layers on Si by UHV-CVD	428/446	21
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20020160584 A1	Semiconductor wafer and method for fabricating the same	438/478	12
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6750119 B2	Epitaxial and polycrystalline growth of Si _{1-x-y} GexCy and Si _{1-y} Cy alloy layers on Si by UHV-CVD	438/479	19
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6645836 B2	Method of forming a semiconductor wafer having a crystalline layer thereon containing silicon, germanium and carbon	438/509	13
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6399993 B1	Semiconductor device and method for fabricating the same	257/370	30

	U	1	Document ID	Title	Current OR	Pages
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6030894 A	Method for manufacturing a semiconductor device having contact plug made of Si/SiGe/Si	438/675	18

	U	1	Document ID	Title	Current OR	Pages
13	<input type="checkbox"/>	<input type="checkbox"/>	US 5909059 A	Semiconductor device having contact plug and method for manufacturing the same	257/750	18
14	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 10256153 A	METHOD FOR CONVERTING AMORPHOUS SI LAYER TO SINGLE CRYSTAL AT LOW TEMPERATURE		11
15	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 10256153 A	Crystallisation of non-crystal silicon@ layer for semiconductor LSI manufacture - involves maintaining predetermined oxygen density and hydrogen concentration in non-crystal silicon@ layer		11